

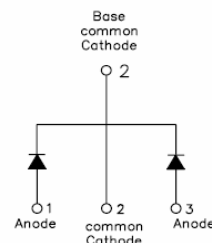
MBR3060CTP SCHOTTKY RECTIFIER

Applications:

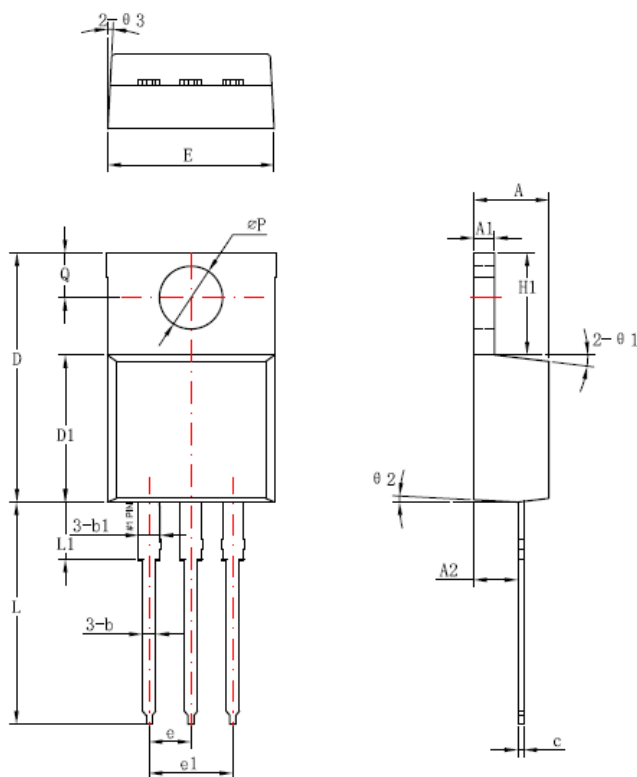
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 150 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



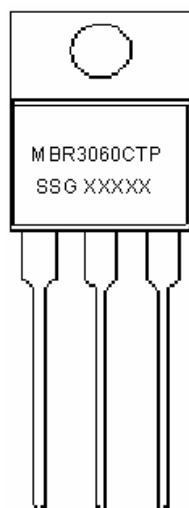
Mechanical Dimensions: In mm



Symbol	Dimensions in millimeters		
	Min	Typical	Max
A	4.42	4.57	4.72
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
D	14.94	15.24	15.54
D1	8.85	9.00	9.15
E	10.01	10.16	10.31
e		2.54	
e1		5.06	
H1	6.04	6.24	6.44
L	12.7	13.56	13.78
L1		3.5	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
Θ1		7°	
Θ2		3°	
Θ3		4°	

TO-220AB

Marking Diagram:



Where XXXXX is YYWWL

MBR = Device Type
 30 = Forward Current (30A)
 60 = Reverse Voltage (60V)
 CTP = Configuration
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBR3060CTP	TO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	60	V
Max. Average Forward	$I_F (AV)$	50% duty cycle @Tc=95°C, rectangular wave form	30	A
Max. Peak One Cycle Non-Repetitive Surge Current (Per leg)	I_{FSM}	8.3ms, Half Sine pulse	200	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop(per leg)*	V _{F1}	@ 15A, Pulse, T _J = 25 °C	0.77	V
	V _{F2}	@ 15 A, Pulse, T _J = 125 °C	0.67	V
Max. Reverse Current*	I _{R1}	@ V _R = rated V _R T _J = 25°C	1.0	mA
	I _{R2}	@ V _R = rated V _R T _J = 125°C	100	mA
Max. Junction Capacitance (per leg)	C _T	@ V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	700	pF
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

* Pulse Width < 300μs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T _J	-	-55 to +150	°C
Max. Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case	R _{θJC}	DC operation	3.0	°C/W
Maximum Thermal Resistance, Case to Heat Sink	R _{θJA}	DC operation	60	°C/W
Approximate Weight	wt	-	2	g
Case Style	TO-220AB			

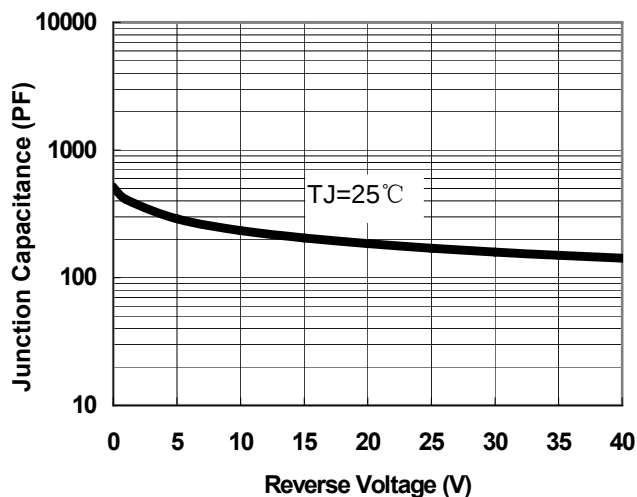


Fig.1-Typical Junction Capacitance

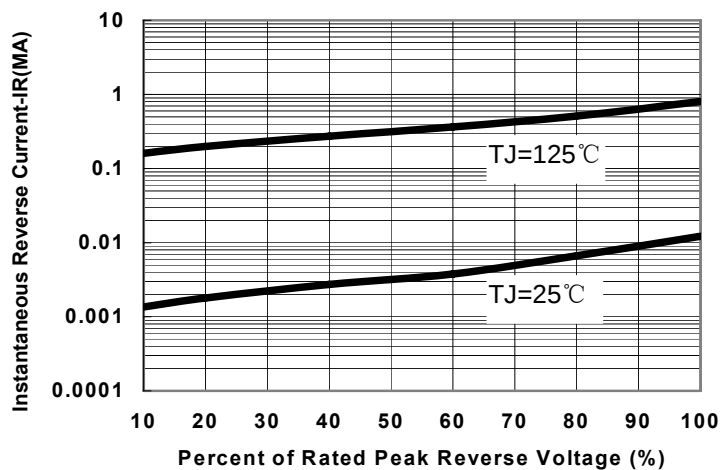


Fig.2-Typical Reverse Characteristics

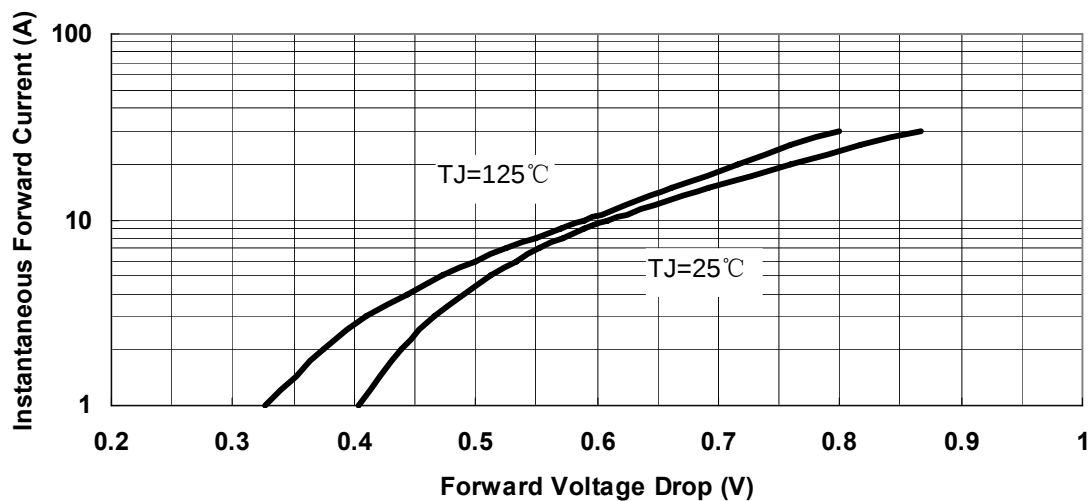


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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